

2SC3679

Silicon NPN Triple Diffused Planar Transistor (High Voltage Switching Transistor)

Application : Switching Regulator and General Purpose

Absolute maximum ratings (Ta=25°C)

Symbol	2SC3679	Unit
VCBO	900	V
VCEO	800	V
VEBO	7	V
IC	5(Pulse10)	A
IB	2.5	A
Pc	100(Tc=25°C)	W
TJ	150	°C
Tstg	-55 to +150	°C

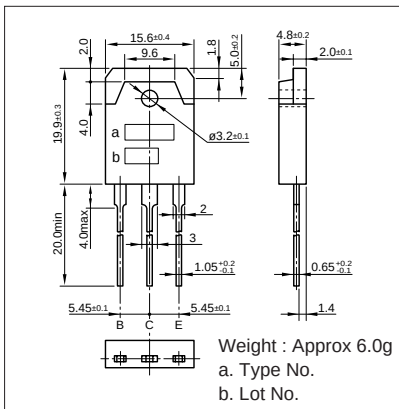
Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SC3679	Unit
ICBO	VCB=800V	100max	μA
IEBO	VEB=7V	100max	μA
V(BR)CEO	IC=10mA	800min	V
hFE	VCE=4V, IC=2A	10to30	
VCE(sat)	IC=2A, IB=0.4A	0.5max	V
VBE(sat)	IC=2A, IB=0.4A	1.2max	V
fr	VCE=12V, IE=-0.5A	6typ	MHz
COB	VCB=10V, f=1MHz	75typ	pF

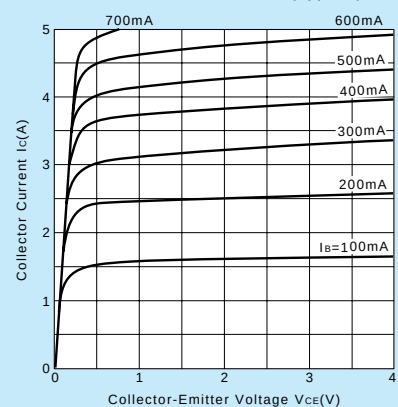
Typical Switching Characteristics (Common Emitter)

VCC (V)	RL (Ω)	IC (A)	VBB1 (V)	VBB2 (V)	IB1 (A)	IB2 (A)	ton (μs)	tstg (μs)	tf (μs)
250	125	2	10	-5	0.3	-1	1max	5max	1max

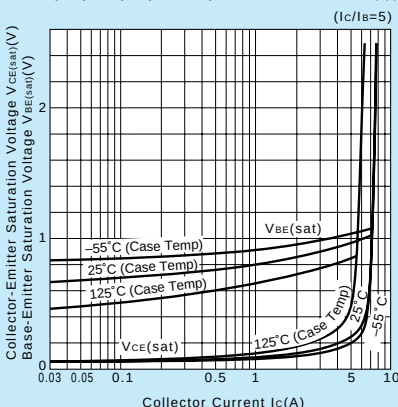
External Dimensions MT-100(TO3P)



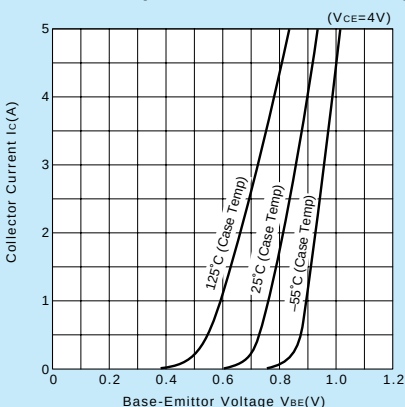
IC-VCE Characteristics (Typical)



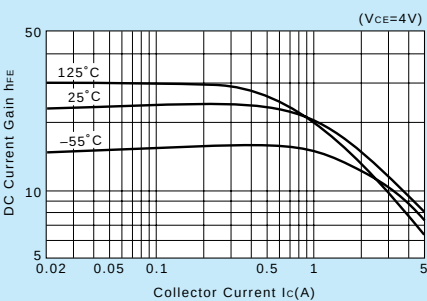
VCE(sat), VBE(sat)-IC Temperature Characteristics (Typical)



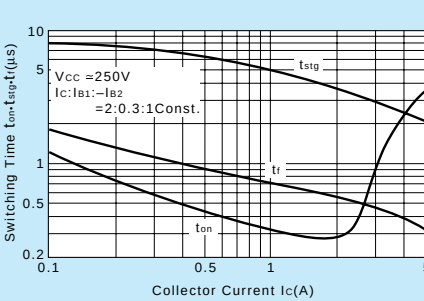
IC-VBE Temperature Characteristics (Typical)



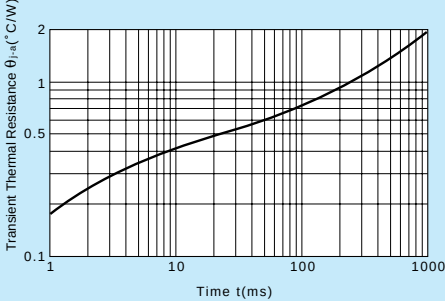
hFE-IC Characteristics (Typical)



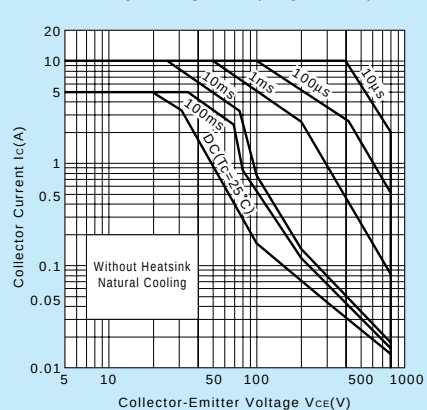
ton•tstg•tr-IC Characteristics (Typical)



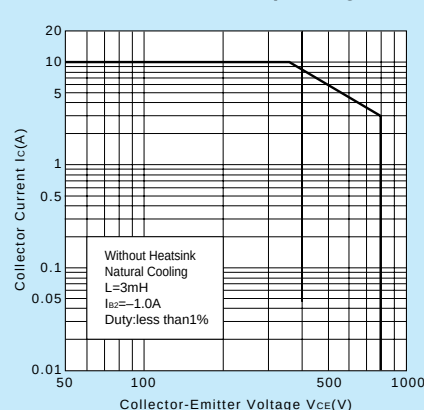
θj-a-t Characteristics



Safe Operating Area (Single Pulse)



Reverse Bias Safe Operating Area



Pc-Ta Derating

